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CM6200

Advance Information

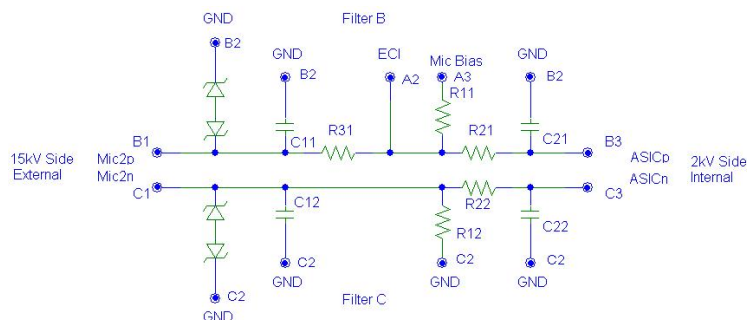
EMI Filters with ESD Protection for Microphone Interface

Description

ON Semiconductor's CM6200 is a 3x3, 8-bump EMI filter with ESD protection device for microphone interface applications in a CSP form factor, 0.4 mm pitch. The CM6200 is fully compliant with IEC 61000-4-2 and is also RoHS II compliant.

Features

- This Device is Pb-Free, Halogen Free/BFR Free and is RoHS Compliant



Note: B2 and C2 are ground pins and should be connected together on the PCB

Figure 1. Electrical Schematic



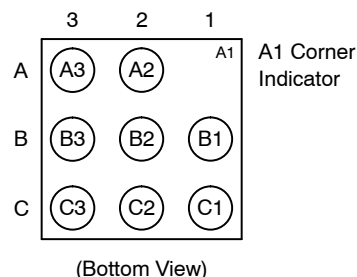
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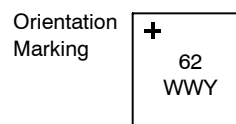


WLCSP-8
PLASTIC
CASE 567CF

PACKAGE PINOUT



MARKING DIAGRAM



62 = CM6200
WWY = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

This document contains information on a new product. Specifications and information herein are subject to change without notice.

CM6200

Pin Information

Table 1. PIN DESCRIPTIONS

Pin	Description	Pin	Description
A2	ECI	B3	ASICp (Internal)
A3	Mic_Bias	C1	Mic2n (External)
B1	Mic2p (External)	C2	GND
B2	GND	C3	ASICn (Internal)

Electrical Specifications and Conditions

Table 2. PARAMETERS AND OPERATING CONDITIONS

Parameter	Rating	Units
Storage Temperature Range	-55 to +150	°C
Operating Temperature Range	-40 to +85	°C

Table 3. ELECTRICAL OPERATING CHARACTERISTICS (Note 1)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
R11	Bias Resistance		1.9	2.0	2.1	kΩ
R12	Resistance		0.8	1.0	1.2	kΩ
R21	Resistance		1.76	2.20	2.64	kΩ
R22	Resistance		1.76	2.20	2.64	kΩ
R31	Resistance		20	25	30	Ω
C11, C12	Pin Capacitance	At 1 MHz, $V_{IN} = 0$ V	0.67	0.83	1.0	nF
C21, C22	Pin Capacitance	At 1 MHz, $V_{IN} = 0$ V	1.0	1.25		nF
I_{LEAK_B}	Leakage Current from Pins B1 to B2	$V_{IN} = 5$ V; B3, A2 and A3 floating. C1, C2, and C3 grounded.		1.0	100	nA
I_{LEAK_C}	Diode Leakage Current from Filter C	$V_{IN} = 5$ V; (Note 3)		1.0		nA
V_B	Breakdown Voltage (Positive)	$I_f = +1$ mA (Filter B only); (Note 3)	13			V
	Breakdown Voltage (Negative)	$I_f = -1$ mA (Filter B only); (Note 3)			-13	V
V_{ESD}	ESD Protection Peak Discharge Voltage at B1 and C1 pins a) Contact discharge per IEC 61000-4-2 standard and b) Air discharge per IEC 61000-4-2 standard	(Note 2)	±15 ±15			kV
	ESD Protection Peak Discharge Voltage at A2, A3, B3, and C3 pins a) Contact discharge per IEC 61000-4-2 standard and b) Air discharge per IEC 61000-4-2 standard	(Note 2)	±2 ±2			kV

1. All parameters specified at $T_A = 25^\circ\text{C}$ unless otherwise noted.
2. Standard IEC 61000-4-2 with $C_{Discharge} = 150$ pF, $R_{Discharge} = 330$ Ω.
3. Filter C parameters are guaranteed by similarity to Filter B.

Performance Information

Simulation

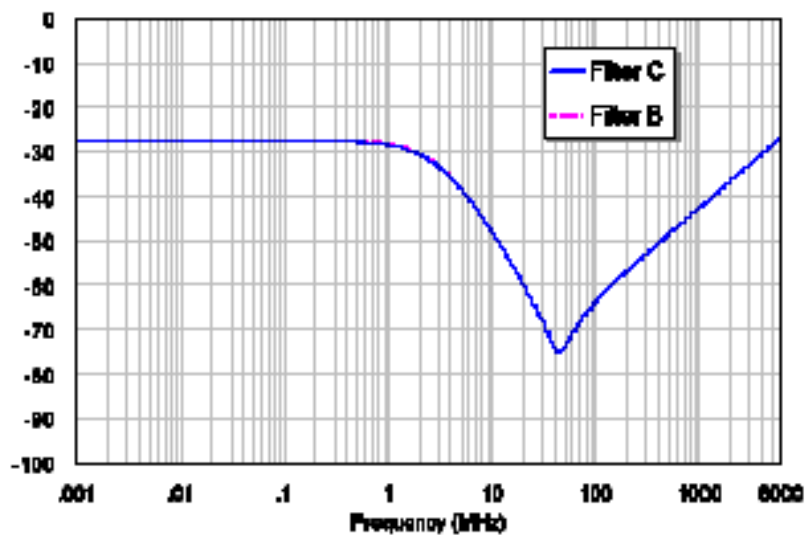


Figure 2. Typical Insertion Loss (Bias = 0 V, $T_A = 25^\circ\text{C}$; $50\ \Omega$ Environment)

RF Characteristics

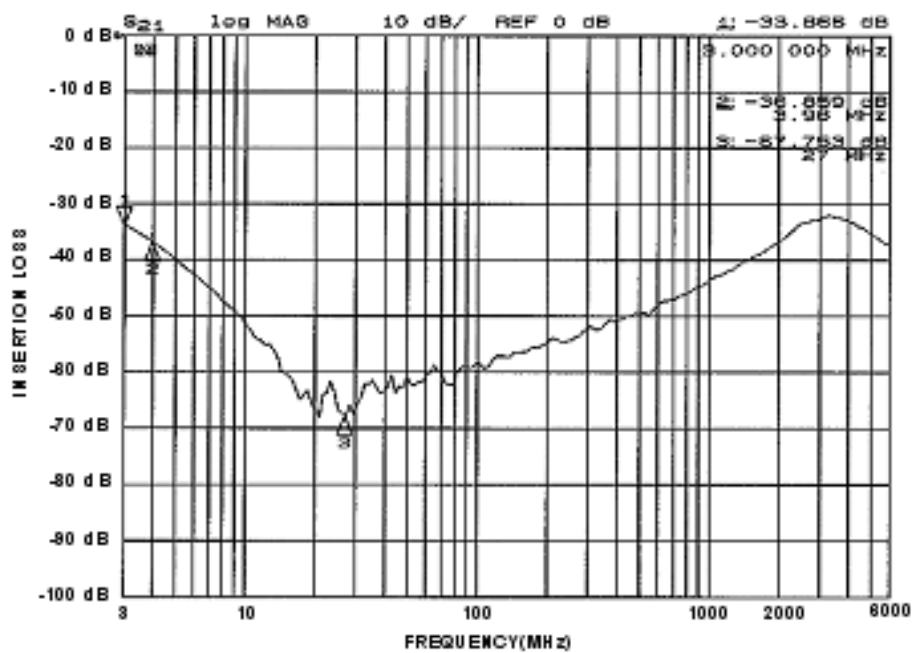


Figure 3. Typical Insertion Loss for Filter B (Bias = 0 V, $T_A = 25^\circ\text{C}$; $50\ \Omega$ Environment); Pins A2 and A3 Floating

RF Characteristics

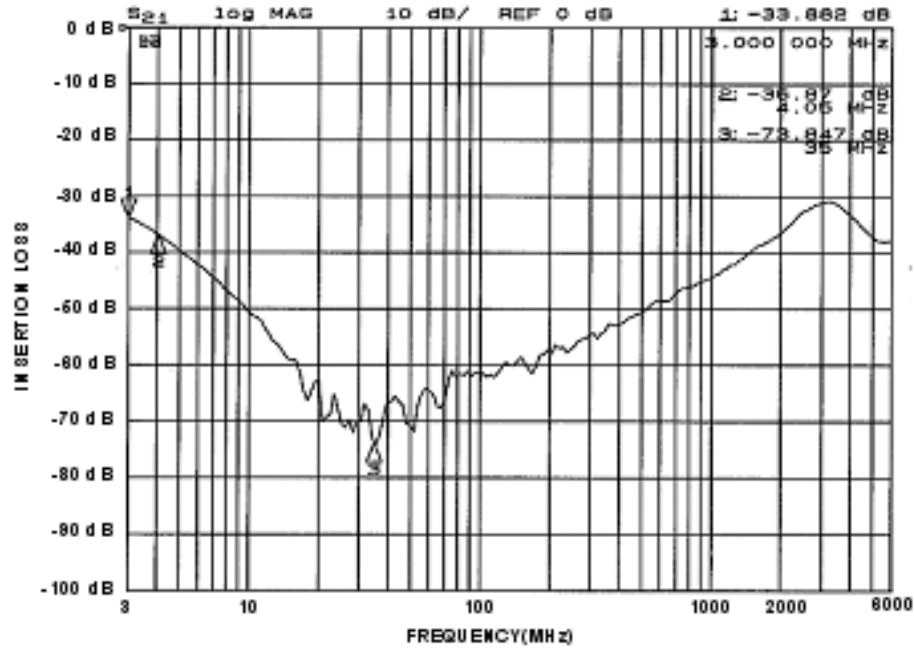


Figure 4. Typical Insertion Loss for Filter C (Bias = 0 V, $T_A = 25^\circ\text{C}$; $50\ \Omega$ Environment)

Vertical Structure Specification*

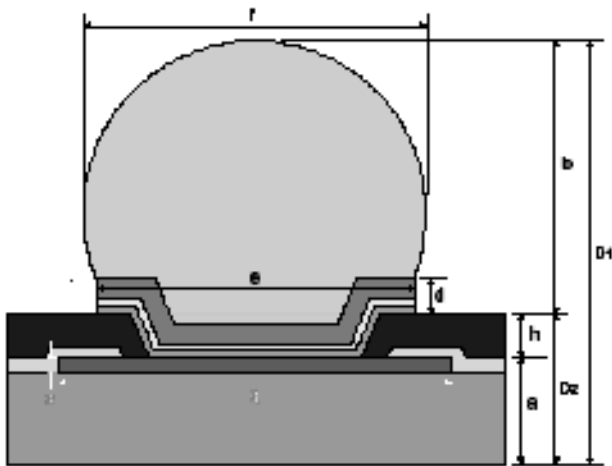


Figure 5. Sectional View

VERTICAL STRUCTURE DIMENSIONS (nominal)

Ref.	Parameter	Material	Dimension
a	Die Thickness	Silicon	396 μm
h	Repassivation	Polyimide	10 μm
d	UBM-(Ti/Cu)	Plated Cu	7.0 μm
		Sputtered Cu	0.4 μm
		Sputtered Ti	0.1 μm
e	UBM Wetting Area Diameter		240 μm
b	Bump Standoff		194 μm
f	Solder Bump Diameter after Bump Reflow		270 μm
c	Metal Pad Height	AlSiCu	1.5 μm
g	Metal Pad Diameter		310 μm
D2			0.406 mm
D1	Finished Thickness		0.600 mm

*Daisy Chain CM6000

CM6200

Table 4. CSP TAPE AND REEL SPECIFICATIONS †

Part Number	Chip Size (mm)	Pocket Size (mm) $B_0 \times A_0 \times K_0$	Tape Width W	Reel Dia.	Qty Per Reel	P_0	P_1
CM6200	1.20 X 1.20 X 0.60	1.346 X 1.346 X 0.729	8 mm	178 mm (7")	5000	4 mm	4 mm

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

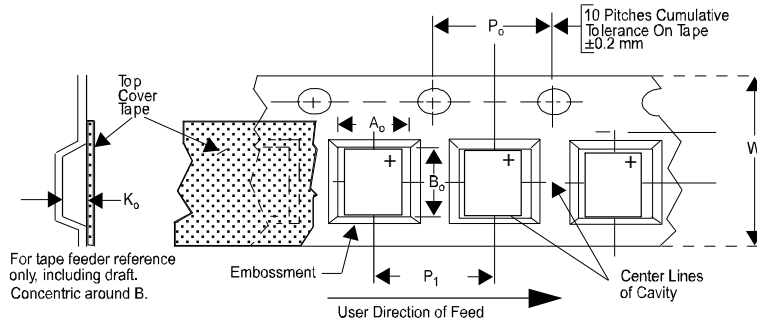


Figure 6. Tape and Reel Mechanical Data

